

Investigation of annealing effect on the forward bias and leakage current changes of P-Type 6H-SiC schottky diodes with SiO₂ ramp profile after irradiated UP To 1.75 MGY (Application for nuclear fuel elements facilities)

Deskripsi Lengkap: <https://lib.ui.ac.id/detail?id=128989&lokasi=lokal>

Abstrak

Annealing effect on the electrical properties change of P - type 6H-SiC schottky diodes with SiO₂ ramp profile after irradiated up to 1.75 MGy at RT (Room Temperature) were investigated. A perpendicular edge termination based on oxide ramp profile around the schottky contact is used on Al schottky rectifier fabricated on a 10 um p--type 6H-SiC epi-layer on P-type 6H-SiC substrate (3.5 off, Si face) Na : $5.9 \times 10^{15}/\text{cm}^2$